

ad 77.(New) An electrically non-volatile multi-level memory device according to claim 75, wherein each of said plurality of memory cells has a source region to which is supplied with a reference potential in said read operation.--

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REMARKS

The present application, at page 11, lines 27-31, incorporates by reference another application entitled "Multi-State EEprom Read and Write Circuits and Techniques", filed on the same day as the initial parent to the present application, namely April 13, 1989, by Sanjay Mehrotra and Eliyahou Harari, two of the inventors who are also named in the present application. This incorporated application is Serial No. 07/337,579, now abandoned, continuations-in-part of which have issued as patents nos. 5,163,021 and 5,172,338. A primary purpose of the present amendment is to insert a majority of the incorporated Serial No. 07/337,579 into the present application in order to support claims based thereon that are also being added by this Preliminary Amendment.

Therefore, essentially all of the Summary of the Invention, Brief Description of the Drawings and Description of the Preferred Embodiments sections of Serial No. 07/337,579 are being added to the present application. A major revision that has been made to this added text is a change in the drawing figure numbers. Figures 1-17 of Serial No. 07/337,579 are being renumbered herein as figures 9-25, respectively, in order not to use any of the same figure numbers previously used in the present application. Tables 1 and 2 of the incorporated application have also been relabeled as figures 26 and 27, respectively. Further, the reference numbers of the drawings have been changed by adding 1000 to the reference numbers of the figures being incorporated from Serial No. 07,337,579, in order to avoid duplicating the reference numbers already used in the original figures of the present application. Corresponding changes have been made to the text of Serial No. 07/337,579 that is being inserted into the present

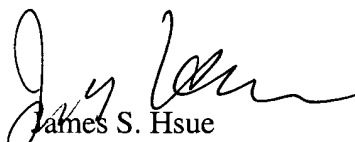
Claims 63-77 being added by this Amendment are substantial copies of claims 1, 3-4, 6, 13, 15-17, 19-20, and 29-33, respectively, of U.S. Patent No. 6,014,327 - Banks, granted January 11, 2000, a copy of which is being filed herewith. These claims are directed to the use program verify in a system with multi-state memory elements. The copied claims of the present application differ from the originals in the Banks patent in that they do not specify the

phenomenon of hot electron injection for injecting electrons into the floating gate. Claims 63-72 being added by this Amendment are also substantial copies of claims 7, 9-10, 12, 21, 23-25, and 27-28, respectively, of the Banks patent, as claims 1, 3, 4, 6, 13, 15, 16, 17, 19, and 20 respectively differ from claims 7, 9, 10, 12, 21, 23, 24, 25, 27, and 28 of the Banks patent in that the preamble of the independent claims of the first group specify the phenomenon of hot electron injection for injecting electrons into the floating gate, while the preamble of the independent claims of the second group specify the phenomenon of Fowler-Nordheim tunneling for injecting electrons into the floating gate. Claims 63-77 have been modified to not specify one of these mechanisms over the other. Additionally, claims 64, 66, 68, and 71 have had their dependence changed from the original. A prompt examination and allowance of the present continuation application is solicited.

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